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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>		<b>Application Number</b>	10/582,392
(use as many sheets as necessary)		<b>Filing Date</b>	June 28, 2007
Sheet 1 of 1		<b>First Named Inventor</b>	Horsky et al.
		<b>Group Art Unit</b>	2821
		<b>Examiner Name</b>	Bernard Souw
		<b>Attorney Docket Number</b>	211843-00044

<b>U.S. PATENT DOCUMENTS</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
/B.S./	A1	5,497,006	03-05-1996	Sferlazzo	
	A2	2008-0121811	05-29-2008	Horsky	
	A3	2004-0002202	01-01-2004	Horsky	
/B.S./	A4	2008-0223409	04-18-2008	Horsky	
	A5	12/234,202	09-19-2008	Horsky	

<b>FOREIGN PATENT DOCUMENTS</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
/B.S./	B1	WO 2005/059942 A2			T <sup>6</sup>
/B.S./	B2	WO 2004/003973 A3			T <sup>6</sup>

<b>OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS</b>					
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher city and/or country where published			T <sup>2</sup>
/B.S./	C1	E.J. Collart et al., "Co-Implantation with Conventional Spike Anneal Solutions for 45 nm Ultra-Shallow Junction Formation", Proceedings of the Eight International Workshop on: Fabrication, Characterization and Modeling Of Ultra-Shallow Doping Profiles in Semiconductors, June 2005, p. 327			
	C2	S.Rizk et al., "Modeling the Suppression Boron Diffusion in Si/SiGe Due to Carbon Incorporation", ibid, p. 315			
	C3	L.S. Robertson et al., "The Effect of Impurities and Activation of Ion Implanted boron in Silicon", Mat. Res. Soc. Symp. Vol. 610, pp. B5.8.1-B5.8.6 (2000)			
	C4	Mare E. Law et al., "Influence of Carbon on the diffusion of Interstitials and Boron in Silicon", ibid, pp. B7.4.1-B7.4.5			
	C5	P.A. Stolk et al., "Understanding and Controlling Transient Enhanced Dopant Diffusion in Silicon", Mat. Res. Soc. Symp. Proc. Vol. 354, pp. 307-318 (1995)			
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	C7	Jorg K.N. Lindner et al., "Ion Beam Synthesis of Buried SiC Layers in Silicon: Basic Physical Processes", Nuclear Instruments and Methods Research B 178 (2001) pp. 44-54			
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/B.S./	C10	Masahiro et al., "B-SiC Formation by Low-Energy Ion-Doping Technique", Japanese Journal of Applied Physics Vol. 29, No. 8, August, 1990, pp. L 1493 - L 1496			
<b>Examiner Signature</b>		/Bernard Souw/			03/04/2009

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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